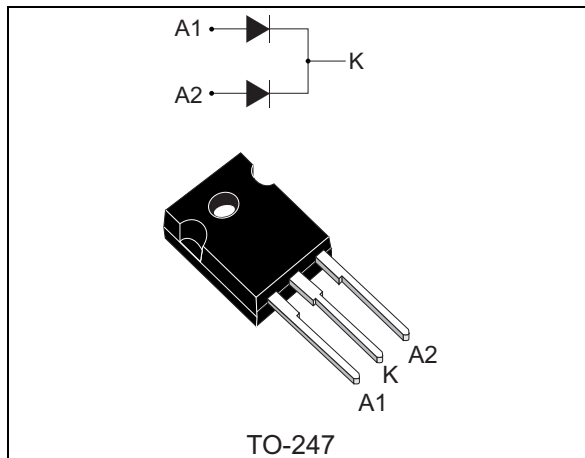


Turbo 2 ultrafast high voltage rectifier

Datasheet – production data



Features

- Ultrafast switching
- Low reverse recovery current
- Reduces switching losses
- Low thermal resistance
- ECOPACK[®]2 compliant component

Description

The STTH60SW03C uses ST Turbo 2 300 V technology. It is especially suited to be used for DC/DC and DC/AC converters in the secondary stage of MIG/MMA/TIG welding machines.

Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 30A
V_{RRM}	300 V
t_{rr} (typ)	20 ns
V_F (typ)	1.05 V
T_j (max)	175 °C

1 Characteristics

Table 2. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			300	V
$I_{F(RMS)}$	Forward rms current			45	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$ square waveform	$T_C = 85\text{ °C}$	Per diode	30	A
		$T_C = 75\text{ °C}$	Per device	60	
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal		200	A
T_{stg}	Storage temperature range			-65 to +175	°C
T_j	Maximum operating junction temperature			175	°C

Table 3. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.8	°C/W
		Total	1	
$R_{th(c)}$	Coupling		0.2	

When diodes 1 and 2 are used simultaneously:

$$T_{j(diode1)} = P_{(diode1)} \times R_{th(j-c)}(\text{per diode}) + P_{(diode2)} \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$			15	μA
		$T_j = 125\text{ °C}$			15	150	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 30\text{ A}$			1.55	V
		$T_j = 150\text{ °C}$			1.05	1.25	
		$T_j = 25\text{ °C}$	$I_F = 60\text{ A}$			1.85	
		$T_j = 150\text{ °C}$			1.35	1.6	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.89 \times I_{F(AV)} + 0.012 I_{F(RMS)}^2$$

Table 5. Recovery characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 1\text{ A}, V_R = 30\text{ V},$ $di_F/dt = -100\text{ A}/\mu\text{s}$		20	27	ns
I_{RM}	Reverse recovery current	$T_j = 125\text{ }^\circ\text{C}$	$I_F = 30\text{ A}, V_R = 200\text{ V},$ $di_F/dt = -200\text{ A}/\mu\text{s}$		7	9	A
Q_{rr}	Reverse recovery charge				190		nC
S_{factor}	Softness factor				0.3		
t_{fr}	Forward recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 30\text{ A}, V_{FR} = 1.6\text{ V},$ $di_F/dt = +400\text{ A}/\mu\text{s}$			180	ns
V_{FP}	Forward recovery voltage				3.5	5	V

Figure 1. Average forward power dissipation versus average forward current (per diode)

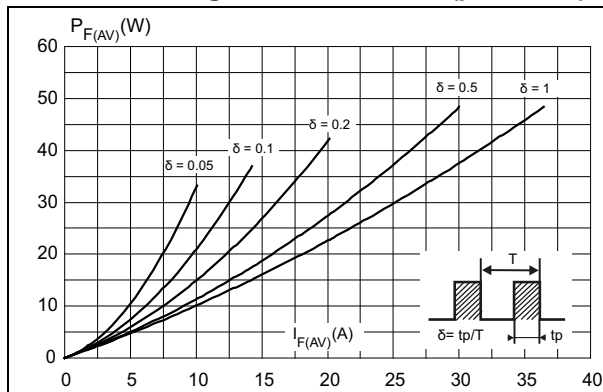


Figure 2. Forward voltage drop versus forward current (typical values, per diode)

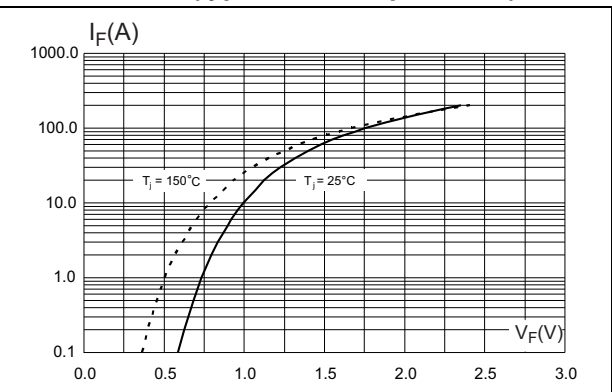


Figure 3. Forward voltage drop versus forward current (maximum values, per diode)

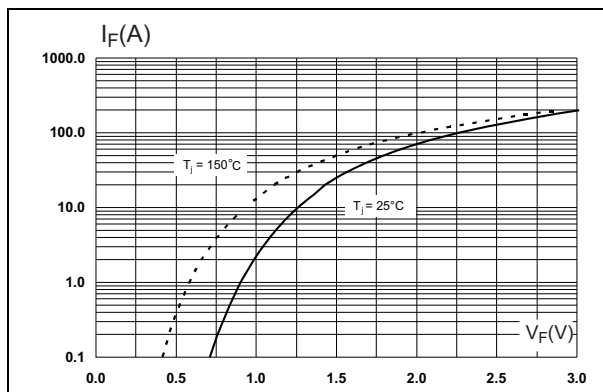


Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration

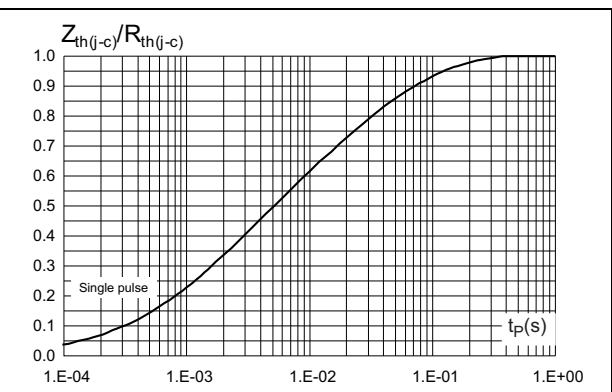


Figure 5. Peak reverse recovery current versus di_F/dt (typical values, per diode)

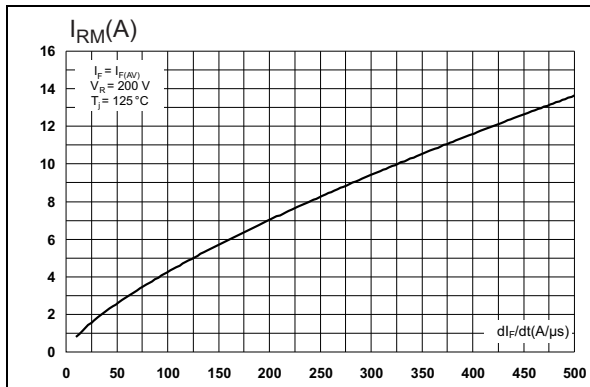


Figure 6. Reverse recovery time versus di_F/dt (typical values, per diode)

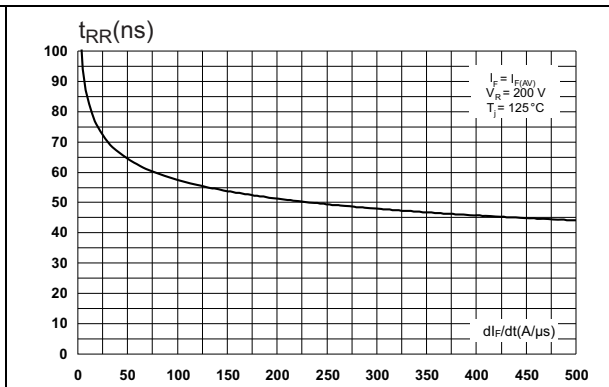


Figure 7. Reverse recovery charges versus di_F/dt (typical values, per diode)

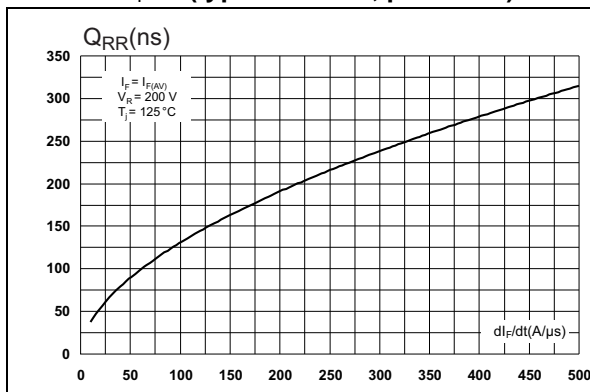


Figure 8. Reverse recovery softness factor versus di_F/dt (typical values, per diode)

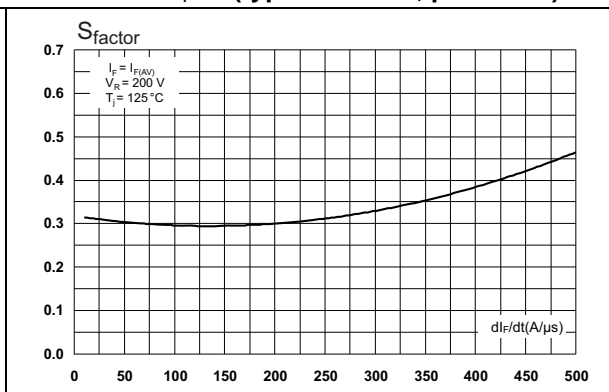


Figure 9. Relative variations of dynamic parameters versus junction temperature

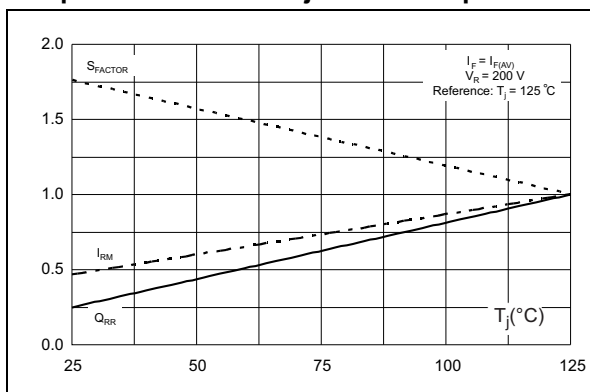


Figure 10. Transient peak forward voltage versus di_F/dt (typical values, per diode)

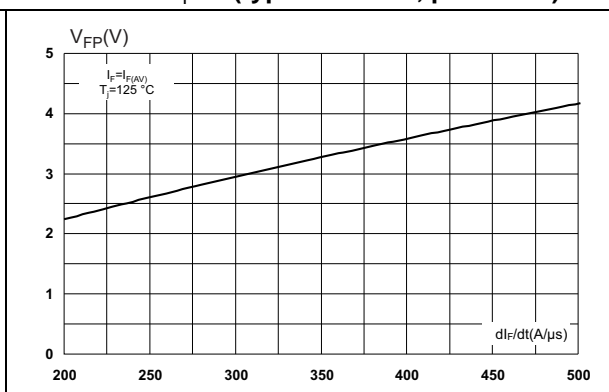


Figure 11. Forward recovery time versus di_F/dt (typical values, per diode)

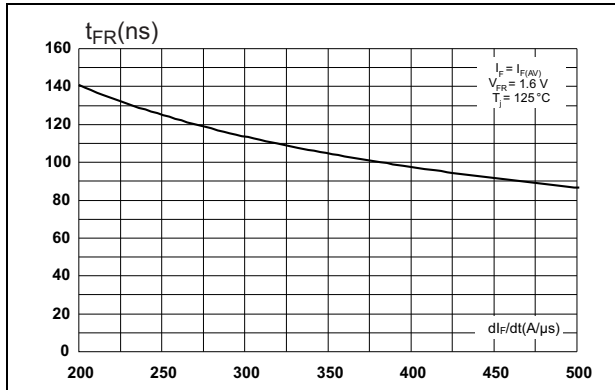
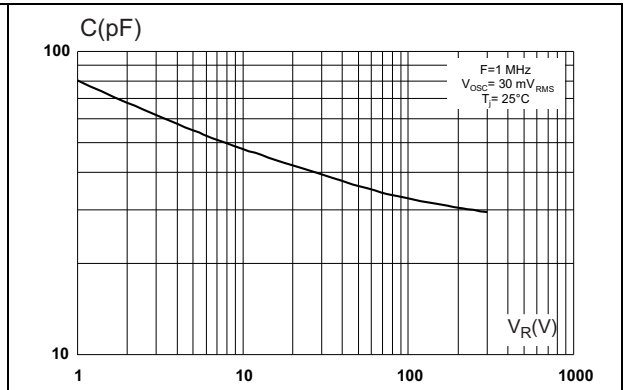


Figure 12. Junction capacitance versus reverse voltage applied (typical values, per diode)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque: TO-247 0.5 to 1.0 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 13. TO-247 dimension definitions

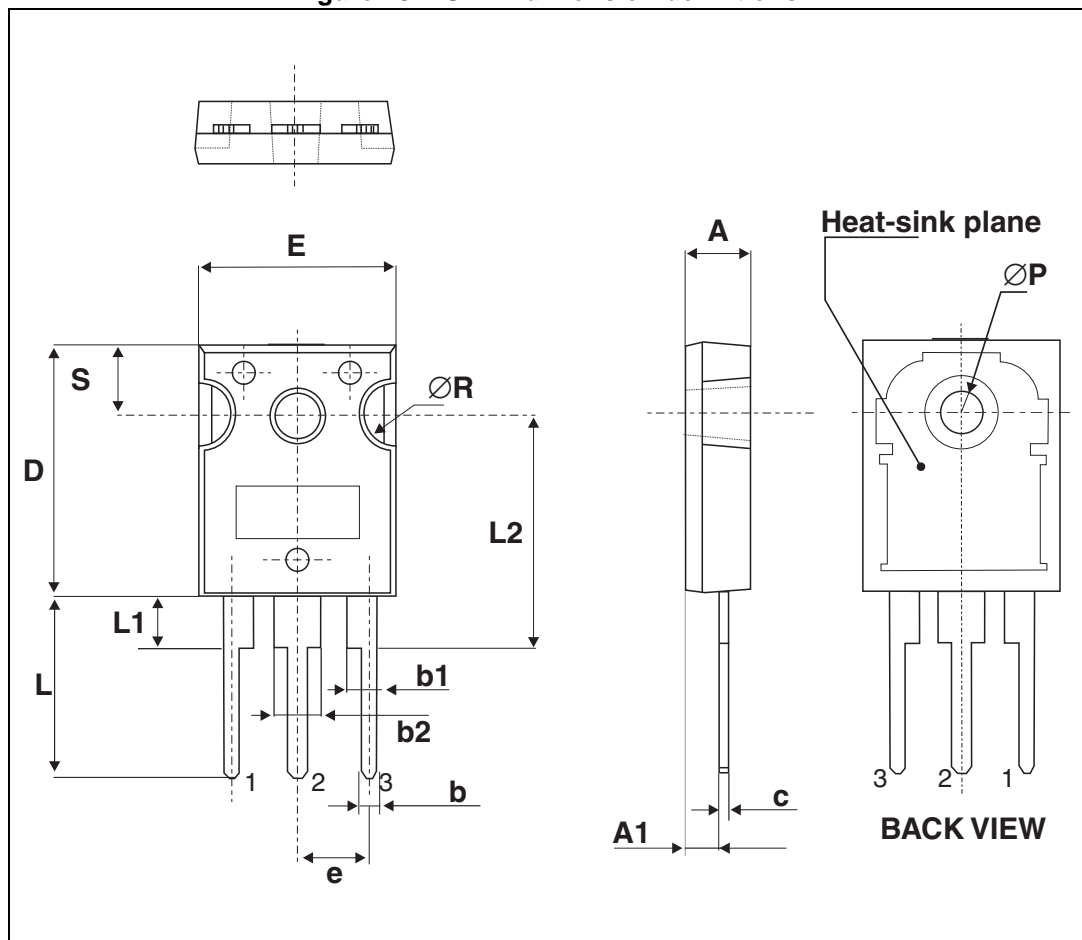


Table 6. TO-247 dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ	Max.
A	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
c	0.40		0.80	0.015		0.031
D ⁽¹⁾	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2	18.50 typ.			0.728 typ.		
∅P ⁽²⁾	3.55		3.65	0.139		0.143
∅R	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

1. Dimension D plus gate protrusion does not exceed 20.5 mm.
2. Resin thickness around the mounting hole is not less than 0.9 mm.

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH60SW03CW	STTH60SW03CW	TO-247	4.46	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
13-Jan-2015	1	First release.

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